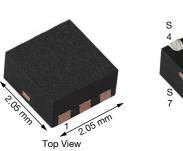
SQA405EJ

www.vishay.com

Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET





Marking Code: QEXXXX

PRODUCT SUMMARY				
V _{DS} (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 V$	0.035			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.050			
I _D (A)	-10			
Configuration	Single			
Package	PowerPAK SC-70			

PowerPAK[®] SC-70-6L Single

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

GO

P-Channel MOSFET

S

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RoHS COMPLIANT HALOGEN FREE

ABSOLUTE MAXIMUM RATING	GS (T _C = 25 °C, unles	s otherwise noted	(k	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-40	v
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	T _C = 25 °C	I	-10	
	T _C = 125 °C	۱ _D	-10	
Continuous source current (diode conduction) ^a		I _S	10	А
Pulsed drain current ^b		I _{DM}	-40	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-15	
Single pulse avalanche energy	L = 0.1 IIIA	E _{AS}	11.25	mJ
Maximum power dissipation ^b	T _C = 25 °C	P	13.6	w
	T _C = 125 °C	P _D	4.5	vv V
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	90	°C/W
Junction-to-case (drain)		R _{thJF}	11	0/10

Notes

a. Package limited

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. When mounted on 1" square PCB (FR4 material)

1



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	·	•				•		
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-40	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		-2.0	-2.5		
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1		
	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	-50	μA	
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	-150		
On-state drain current ^a	I _{D(on)}	$V_{GS} = -10 V$	$V_{DS} \ge 5 V$	-8	-	-	Α	
Drain-source on-state resistance ^a		$V_{GS} = -10 V$	I _D = -5 A	-	0.027	0.035	Ω	
	Р	$V_{GS} = -10 V$	I _D = -5 A, T _J = 125 °C	-	-	0.067		
	R _{DS(on)}	V _{GS} = -10 V	l _D = -5 A, T _J = 175 °C	-	-	0.080		
		$V_{GS} = -4.5 V$	I _D = -4 A	-	0.038	0.050		
Forward transconductance b	9 _{fs}	V _{DS} :	= -10 V, I _D = -7 A	-	18	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = -25 V, f = 1 MHz	-	1450	1815	pF	
Output capacitance	C _{oss}	V _{GS} = 0 V		-	105	131		
Reverse transfer capacitance	C _{rss}			-	92	115		
Total gate charge ^c	Qg			-	26	33		
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -20 \text{ V}, \text{ I}_{D} = -8 \text{ A}$	-	4.1	-	nC	
Gate-drain charge c	Q _{gd}			-	4.8	-		
Gate resistance	Rg	f = 1 MHz		4.4	7.4	11.8	Ω	
Turn-on delay time ^c	t _{d(on)}			-	9	15		
Rise time ^c	t _r	V_{DD} = -20 V, R _L = 8 Ω I _D \cong -2.5 A, V _{GEN} = -10 V, R _g = 1 Ω		-	4	8	ns	
Turn-off delay time ^c	t _{d(off)}			-	36	55		
Fall time ^c	t _f			-	10	16		
Source-Drain Diode Ratings and Char	acteristics	·						
Pulsed current ^a	I _{SM}			-	-	-40	Α	
Forward voltage	V _{SD}	$I_{\rm F} = -5$ A, $V_{\rm GS} = 0$		_	-0.84	-1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

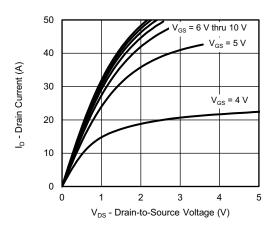
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

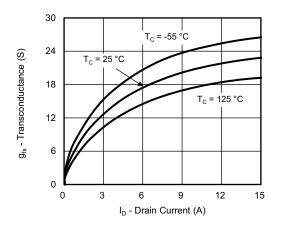


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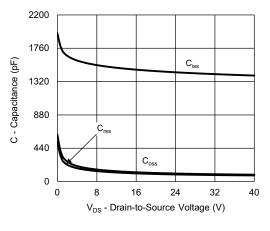
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



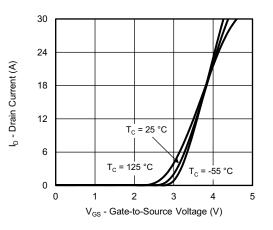
Output Characteristics



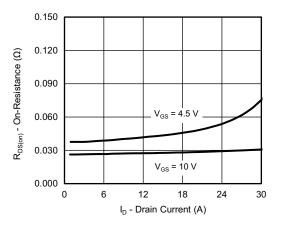
Transconductance



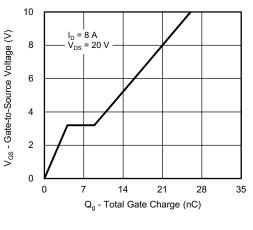
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

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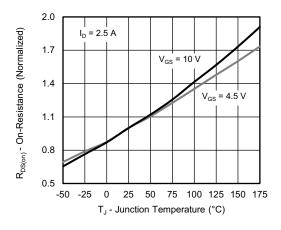
3 s. contact: automostech Document Number: 76032

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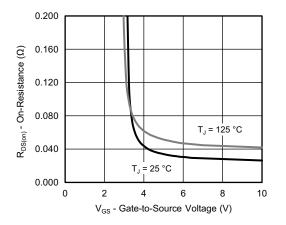


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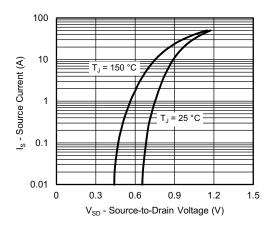
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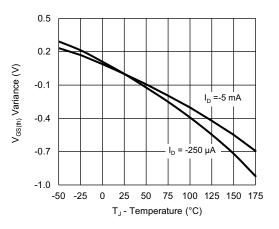
On-Resistance vs. Junction Temperature



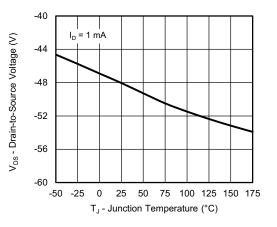
On-Resistance vs. Gate-to-Source Voltage



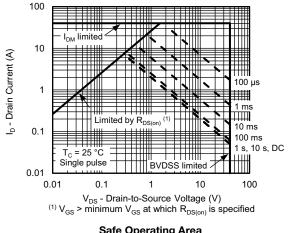
Source-Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

S18-0238-Rev. A, 26-Feb-18

4

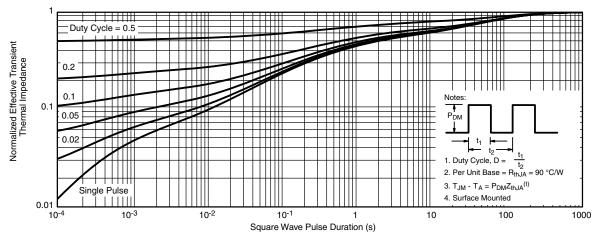
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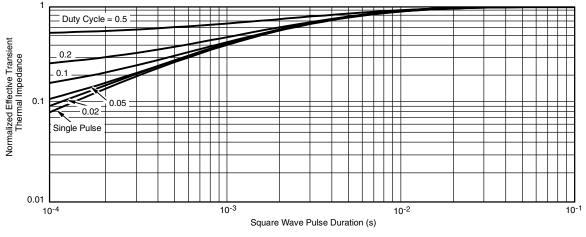


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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

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RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

Return to Index



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